





















Fig. 6.  $E_x$  field distribution of the quasi-TE mode at the center of the  $\text{Si}_3\text{N}_4$  strip waveguide are shown. On the Y-axis the  $E_x$  field amplitude are marked at critical material interfaces (a) Air clad  $\text{Si}_3\text{N}_4$  wire showing a high  $E_x$  field amplitude at the rough,  $\text{Si}_3\text{N}_4$ -air material interface. (b)  $\text{Al}_2\text{O}_3$  clad  $\text{Si}_3\text{N}_4$  wire showing a lower  $E_x$  field amplitude at the rough,  $\text{Si}_3\text{N}_4$ -air material interface and a higher  $E_x$  field amplitude at the less rough  $\text{Al}_2\text{O}_3$ -air interface.

With ALD deposition, the optical mode fill-factor within the  $\text{Si}_3\text{N}_4$  wire increases to 0.58 from 0.49 with air cladding (simulation results in Table 4). The increased optical mode confinement reduces the impact of surface roughness on the optical mode loss in the case of ALD clad waveguide.

Table 4. Comparison of fill factors in air clad and ALD coated  $\text{Si}_3\text{N}_4$  chips.

ALD Clad $\text{Si}_3\text{N}_4$ Chip	Air Clad $\text{Si}_3\text{N}_4$ Chip
$n_{\text{eff}[\text{TE}]} = 1.6054$	$n_{\text{eff}[\text{TE}]} = 1.5654$
Fill Factor $_{\text{Si}_3\text{N}_4} = 0.5805$	Fill Factor $_{\text{Si}_3\text{N}_4} = 0.4933$

While this paper shows results on reduction from extremely high to moderately low propagation loss waveguides, the technique can also be used to reduce scattering losses from moderately low to very low propagation loss  $\text{Si}_3\text{N}_4$  waveguides.

## 5. Conclusion

We demonstrate the impact of ALD-assisted conformal  $\text{Al}_2\text{O}_3$  coating as a simple post-processing method in reducing the scattering loss in the PECVD  $\text{Si}_3\text{N}_4$  wires (220 nm x 500 nm) at VNIR wavelengths. The RMS roughness of the nitride waveguides is reduced from 1.47 nm to 0.5 nm through this ALD coating. As a result, the waveguide loss is reduced from very high values, estimated to be  $\sim 60$  dB/cm, to a moderate 5 dB/cm level at 900 nm wavelength. Both the RMS roughness and waveguide loss achieved after ALD coating is comparable to the values reported before on similar PECVD nitride waveguides at the same wavelength.

## Acknowledgments

We acknowledge Antti Säyöntjoki and Alex Pyymaki Perros from Aalto University for initial ALD studies. Authors also thank Liesbet Van Landschoot from Ghent University for the support to realize FIB/SEM cross-sections. Part of this work is supported by the European Research Council through the ERC Spectra project. This research is also supported by Academy of Finland Grant no. 272155 and 134980 and GETA Graduate School, Finland.